Eric Tourni

List of Publications by Year in Descending Order

271 papers	4,281 citations	34 h-index	47 g-index
300 ext. papers	4,774 ext. citations	2.9 avg, IF	5.24 L-index

#	Paper	IF	Citations
271	Impact of the ridge etching-depth on GaSb-based laser diodes. *Electronics Letters*, **2022**, 58, 162-163	1.1	
270	Characterization and Simulation of AlGaAsSb/GaSb Tandem Solar Cell. *IEEE Journal of Photovoltaics*, **2022**, 1-8	3.7	
269	Mid-infrared III–V semiconductor lasers epitaxially grown on Si substrates. *Light: Science and Applications*, **2022**, 11,	16.7	5
268	GaSb-based laser diodes grown on MOCVD GaAs-on-Si templates. *Optics Express*, **2021**, 29, 11268-11276	3.3	2
267	Thermal performance of GaInSb quantum well lasers for silicon photonics applications. *Applied Physics Letters*, **2021**, 118, 101105	3.4	1
266	Near-Field Thermophotovoltaic Conversion with High Electrical Power Density and Cell Efficiency above 14. *Nano Letters*, **2021**, 21, 4524-4529	11.5	28
265	Modeling and Characterization of an MBE-Grown Concentrator P-N GaSb Solar Cells Using a Pseudo-3D Model. *IEEE Journal of Photovoltaics*, **2021**, 11, 1032-1039	3.7	
264	Selective Area Growth by Hydride Vapor Phase Epitaxy and Optical Properties of InAs Nanowire Arrays. *Crystal Growth and Design*, **2021**, 21, 5158-5163	3.5	1
263	Investigation of AlInAsSb/GaSb tandem cells – A first step towards GaSb-based multi-junction solar cells. *Solar Energy Materials and Solar Cells*, **2021**, 219, 110795	6.4	5
262	InAs-based quantum cascade lasers grown on on-axis (001) silicon substrate. *APL Photonics*, **2020**, 5, 041302	5.2	12
261	Morphological Control of InN Nanorods by Selective Area Growth–Hydride Vapor-Phase Epitaxy. *Crystal Growth and Design*, **2020**, 20, 2232-2239	3.5	4
260	Zinc-blende group III-V/group IV epitaxy: Importance of the miscut. *Physical Review Materials*, **2020**, 4,	3.2	14
259	Etched-cavity GaSb laser diodes on a MOVPE GaSb-on-Si template. *Optics Express*, **2020**, 28, 20785-20793	3.3	3
258	Mid-infrared laser diodes epitaxially grown on on-axis (001) silicon. *Optica*, **2020**, 7, 263	8.6	26
257	3.3 μm interband-cascade resonant-cavity light-emitting diode with narrow spectral emission linewidth. *Semiconductor Science and Technology*, **2020**, 35, 125029	1.8	1
256	Interband mid-infrared lasers **2020**, 91-130		5
255	Optical properties and dynamics of excitons in Ga(Sb, Bi)/GaSb quantum wells: evidence for a regular alloy behavior. *Semiconductor Science and Technology*, **2020**, 35, 025024	1.8	1

254	Molecular-beam epitaxy of GaSb on 6°-offcut (0 0 1) Si using a GaAs nucleation layer. *Journal of Crystal Growth*, **2020**, 529, 125299	1.6	3
253	Indium antimonide photovoltaic cells for near-field thermophotovoltaics. *Solar Energy Materials and Solar Cells*, **2019**, 203, 110190	6.4	11
252	Type I GaSb1-xBix/GaSb quantum wells dedicated for mid infrared laser applications: Photoreflectance studies of bandgap alignment. *Journal of Applied Physics*, **2019**, 125, 205706	2.5	13
251	Terahertz Spectroscopy of Two-Dimensional Semimetal in Three-Layer InAs/GaSb/InAs Quantum Well. *JETP Letters*, **2019**, 109, 96-101	1.2	0
250	Selective growth of ordered hexagonal InN nanorods. *CrystEngComm*, **2019**, 21, 2702-2708	3.3	9
249	Massless Dirac fermions in III-V semiconductor quantum wells. *Physical Review B*, **2019**, 99,	3.3	6
248	Molecular-Beam Epitaxy of Antimonides for Optoelectronic Devices **2019**, 233-246		1
247	Improved efficiency of GaSb solar cells using an Al0.50Ga0.50As0.04Sb0.96 window layer. *Solar Energy Materials and Solar Cells*, **2019**, 200, 110042	6.4	5
246	The Interaction of Extended Defects as the Origin of Step Bunching in Epitaxial III-V Layers on Vicinal Si(001) Substrates. *Physica Status Solidi - Rapid Research Letters*, **2019**, 13, 1900290	2.5	3
245	GaSbBi Alloys and Heterostructures: Fabrication and Properties. *Springer Series in Materials Science*, **2019**, 125-161	0.9	1
244	Molecular-beam epitaxy of GaInSbBi alloys. *Journal of Applied Physics*, **2019**, 126, 155304	2.5	3
243	Micron-sized liquid nitrogen-cooled indium antimonide photovoltaic cell for near-field thermophotovoltaics. *Optics Express*, **2019**, 27, A11-A24	3.3	17
242	Interband cascade Lasers with AlGaAsSb cladding layers emitting at 3.3 μm. *Optics Express*, **2019**, 27, 31425-31434	3.3	6
241	InAs/GaSb thin layers directly grown on nominal (0 0 1)-Si substrate by MOVPE for the fabrication of InAs FINFET. *Journal of Crystal Growth*, **2019**, 510, 18-22	1.6	1
240	GaSb-based solar cells for multi-junction integration on Si substrates. *Solar Energy Materials and Solar Cells*, **2019**, 191, 444-450	6.4	6
239	Midwave infrared barrier detector based on Ga-free InAs/InAsSb type-II superlattice grown by molecular beam epitaxy on Si substrate. *Infrared Physics and Technology*, **2019**, 96, 39-43	2.7	24
238	Microstructure and interface analysis of emerging Ga(Sb,Bi) epilayers and Ga(Sb,Bi)/GaSb quantum wells for optoelectronic applications. *Applied Physics Letters*, **2018**, 112, 151905	3.4	14
237	On the origin of threading dislocations during epitaxial growth of III-Sb on Si(001): A comprehensive transmission electron tomography and microscopy study. *Acta Materialia*, **2018**, 143, 121-129	8.4	7

236	Anti phase boundary free GaSb layer grown on 300 mm (001)-Si substrate by metal organic chemical vapor deposition. *Thin Solid Films*, **2018**, 645, 5-9	2.2	17
235	Transmission electron microscopy of Ga(Sb, Bi)/GaSb quantum wells with varying Bi content and quantum well thickness. *Semiconductor Science and Technology*, **2018**, 33, 094006	1.8	4
234	GaSb Lasers Grown on Silicon Substrate for Telecom Applications **2018**, 625-635		1
233	Mid-IR plasmonic compound with gallium oxide toplayer formed by GaSb oxidation in water. *Semiconductor Science and Technology*, **2018**, 33, 095009	1.8	3
232	Quantum cascade lasers grown on silicon. *Scientific Reports*, **2018**, 8, 7206	4.9	41
231	Universal description of III-V/Si epitaxial growth processes. *Physical Review Materials*, **2018**, 2,	3.2	30
230	AlInAsSb for GaSb-based multi-junction solar cells **2018**,		3
229	LACBED analysis of the chemical composition of compound semiconductor strained layers **2018**, 221-224		
228	Pedestal formation of all-semiconductor gratings through GaSb oxidation for mid-IR plasmonics. *Journal Physics D: Applied Physics*, **2018**, 51, 015104	3	5
227	Investigation of antimonide-based semiconductors for high-efficiency multi-junction solar cells **2018**,		4
226	Interface energy analysis of III□V islands on Si (001) in the Volmer-Weber growth mode. *Applied Physics Letters*, **2018**, 113, 191601	3.4	9
225	Epitaxial Integration of Antimonide-Based Semiconductor Lasers on Si. *Semiconductors and Semimetals*, **2018**, 1-25	0.6	2
224	A Stress-Free and Textured GaP Template on Silicon for Solar Water Splitting. *Advanced Functional Materials*, **2018**, 28, 1801585	15.6	11
223	In situ determination of the growth conditions of GaSbBi alloys. *Journal of Crystal Growth*, **2018**, 495, 9-13	1.6	7
222	Phosphonate monolayers on InAsSb and GaSb surfaces for mid-IR plasmonics. *Applied Surface Science*, **2018**, 451, 241-249	6.7	8
221	Temperature-dependent terahertz spectroscopy of inverted-band three-layer InAs/GaSb/InAs quantum well. *Physical Review B*, **2018**, 97,	3.3	13
220	Electron tomography on III-Sb heterostructures on vicinal Si(001) substrates: Anti-phase boundaries as a sink for threading dislocations. *Scripta Materialia*, **2017**, 132, 5-8	5.6	7
219	Characterization of antimonide based material grown by molecular epitaxy on vicinal silicon substrates via a low temperature AlSb nucleation layer. *Journal of Crystal Growth*, **2017**, 477, 65-71	1.6	10

218	Growth and characterization of AlInAsSb layers lattice-matched to GaSb. *Journal of Crystal Growth*, **2017**, 477, 72-76	1.6	7
217	GaSbBi/GaSb quantum well laser diodes. *Applied Physics Letters*, **2017**, 110, 222106	3.4	40
216	Molecular beam epitaxy and characterization of high Bi content GaSbBi alloys. *Journal of Crystal Growth*, **2017**, 477, 144-148	1.6	32
215	Highly doped semiconductor plasmonic nanoantenna arrays for polarization selective broadband surface-enhanced infrared absorption spectroscopy of vanillin. *Nanophotonics*, **2017**, 7, 507-516	6.3	22
214	Magnetoabsorption of Dirac Fermions in InAs/GaSb/InAs Three-Layer Gapless Quantum Wells. *JETP Letters*, **2017**, 106, 727-732	1.2	3
213	Low-loss orientation-patterned GaSb waveguides for mid-infrared parametric conversion. *Optical Materials Express*, **2017**, 7, 3011	2.6	11
212	Surface-enhanced infrared absorption with Si-doped InAsSb/GaSb nano-antennas. *Optics Express*, **2017**, 25, 26651-26661	3.3	9
211	Plasmonic bio-sensing based on highly doped semiconductors **2017**,		2
210	Anisotropic strain relaxation and growth mode dependence in highly lattice mismatched III-V systems **2017**, 389-392		
209	Room-temperature continuous-wave operation in the telecom wavelength range of GaSb-based lasers monolithically grown on Si. *APL Photonics*, **2017**, 2, 061301	5.2	30
208	Localized surface plasmon resonance frequency tuning in highly doped InAsSb/GaSb one-dimensional nanostructures. *Nanotechnology*, **2016**, 27, 425201	3.4	16
207	X-ray diffraction study of GaSb grown by molecular beam epitaxy on silicon substrates. *Journal of Crystal Growth*, **2016**, 439, 33-39	1.6	27
206	First orientation-patterned GaSb ridge waveguides fabrication and preliminary characterization for frequency conversion in the mid-infrared **2016**,		1
205	Metamorphic III-V semiconductor lasers grown on silicon. *MRS Bulletin*, **2016**, 41, 218-223	3.2	37
204	Terahertz studies of 2D and 3D topological transitions. *Journal of Physics: Conference Series*, **2015**, 647, 012037	0.3	
203	Mid-infrared characterization of refractive indices and propagation losses in GaSb/AlXGa1-XAsSb waveguides. *Applied Physics Letters*, **2015**, 107, 171901	3.4	14
202	GaSb-based composite quantum wells for laser diodes operating in the telecom wavelength range near 1.55-μm. *Applied Physics Letters*, **2015**, 106, 101102	3.4	11
201	Fano-like resonances sustained by Si doped InAsSb plasmonic resonators integrated in GaSb matrix. *Optics Express*, **2015**, 23, 29423-33	3.3	8

200	Silicon surface preparation for III-V molecular beam epitaxy. *Journal of Crystal Growth*, **2015**, 413, 17-24	1.6	22
199	. *IEEE Journal of Selected Topics in Quantum Electronics*, **2014**, 20, 394-404	3.8	85
198	Silicon-on-insulator shortwave infrared wavelength meter with integrated photodiodes for on-chip laser monitoring. *Optics Express*, **2014**, 22, 27300-8	3.3	21
197	Brewster "mode" in highly doped semiconductor layers: an all-optical technique to monitor doping concentration. *Optics Express*, **2014**, 22, 24294-303	3.3	38
196	Recombination channels in 2.4–3.2 μm GaInAsSb quantum-well lasers. *Semiconductor Science and Technology*, **2013**, 28, 015015	1.8	9
195	Mid-IR heterogeneous silicon photonics **2013**,		1
194	Mid-IR GaSb-Based Bipolar Cascade VCSELs. *IEEE Photonics Technology Letters*, **2013**, 25, 882-884	2.2	13
193	Effects of low temperature on the cold start gaseous emissions from light duty vehicles fuelled by ethanol-blended gasoline. *Applied Energy*, **2013**, 102, 44-54	10.7	121
192	All-semiconductor plasmonics for mid-IR applications **2013**,		2
191	Silicon-on-insulator spectrometers with integrated GaInAsSb photodiodes for wide-band spectroscopy from 1510 to 2300 nm. *Optics Express*, **2013**, 21, 6101-8	3.3	57
190	Silicon-based heterogeneous photonic integrated circuits for the mid-infrared. *Optical Materials Express*, **2013**, 3, 1523	2.6	52
189	Mid-IR GaSb-based monolithic vertical-cavity surface-emitting lasers. *Journal Physics D: Applied Physics*, **2013**, 46, 495101	3	4
188	GaSb-based all-semiconductor mid-IR plasmonics **2013**,		3
187	Integrated thin-film GaSb-based Fabry-Perot lasers: towards a fully integrated spectrometer on a SOI waveguide circuit **2013**,		3
186	Atomic structure of tensile-strained GaAs/GaSb(001) nanostructures. *Applied Physics Letters*, **2013**, 102, 102105	3.4	6
185	III–V/Silicon Photonics for Short-Wave Infrared Spectroscopy. *IEEE Journal of Quantum Electronics*, **2012**, 48, 292-298	2	5
184	Mid-Infrared Semiconductor Lasers. *Semiconductors and Semimetals*, **2012**, 183-226	0.6	31
183	Pseudo volume plasmon in arrays of doped and un-doped semiconductors. *Applied Physics A: Materials Science and Processing*, **2012**, 109, 927-934	2.6	

182	Arrays of doped and un-doped semiconductors for sensor applications. *Applied Physics A: Materials Science and Processing*, **2012**, 109, 943-947	2.6	3
181	Online characterization of regulated and unregulated gaseous and particulate exhaust emissions from two-stroke mopeds: a chemometric approach. *Analytica Chimica Acta*, **2012**, 717, 28-38	6.6	36
180	**2012**,		5
179	Selective lateral etching of InAs/GaSb tunnel junctions for mid-infrared photonics. *Semiconductor Science and Technology*, **2012**, 27, 085011	1.8	8
178	Study of evanescently-coupled and grating-assisted GaInAsSb photodiodes integrated on a silicon photonic chip. *Optics Express*, **2012**, 20, 11665-72	3.3	42
177	Single-mode monolithic GaSb Vertical-Cavity Surface-Emitting Laser. *Optics Express*, **2012**, 20, 15540-6	3.3	18
176	Localized surface plasmon resonances in highly doped semiconductors nanostructures. *Applied Physics Letters*, **2012**, 101, 161113	3.4	48
175	Integrated spectrometer and integrated detectors on Silicon-on-Insulator for short-wave infrared applications **2012**,		1
174	Note: a high transmission Faraday optical isolator in the 9.2 □m range. *Review of Scientific Instruments*, **2011**, 82, 096106	1.7	5
173	Heterogeneous GaSb/SOI mid-infrared photonic integrated circuits for spectroscopic applications **2011**,		3
172	Heterogeneous Integration of GaInAsSb p-i-n Photodiodes on a Silicon-on-Insulator Waveguide Circuit. *IEEE Photonics Technology Letters*, **2011**, 23, 1760-1762	2.2	28
171	Continuous-wave operation above room temperature of GaSb-based laser diodes grown on Si. *Applied Physics Letters*, **2011**, 99, 121113	3.4	69
170	Interfacial intermixing in InAs/GaSb short-period-superlattices grown by molecular beam epitaxy. *Applied Physics Letters*, **2010**, 96, 021904	3.4	42
169	Highly tensile-strained, type-II, Ga1□InxAs/GaSb quantum wells. *Applied Physics Letters*, **2010**, 96, 062109	3.4	11
168	GaSb-Based Laser, Monolithically Grown on Silicon Substrate, Emitting at 1.55 mu m at Room Temperature. *IEEE Photonics Technology Letters*, **2010**, 22, 553-555	2.2	58
167	Optical performances of InAs/GaSb/InSb short-period superlattice laser diode for mid-infrared emission. *Journal of Applied Physics*, **2010**, 108, 093107	2.5	12
166	Modelling of an InAs/GaSb/InSb short-period superlattice laser diode for mid-infrared emission by the k.p method. *Journal Physics D: Applied Physics*, **2010**, 43, 325102	3	11
165	Non-random Be-to-Zn substitution in ZnBeSe alloys: Raman scattering and ab initio calculations. *European Physical Journal B*, **2010**, 73, 461-469	1.2	8

164	InAs/GaSb/InSb short-period super-lattice diode lasers emitting near 3.3 [micro sign]m at room-temperature. *Electronics Letters*, **2009**, 45, 165	1.1	11
163	Interface properties of (Ga,In)(N,As) and (Ga,In)(As,Sb) materials systems grown by molecular beam epitaxy. *Journal of Crystal Growth*, **2009**, 311, 1739-1744	1.6	21
162	MBE growth of mid-IR diode lasers based on InAs/GaSb/InSb short-period superlattice active zones. *Journal of Crystal Growth*, **2009**, 311, 1905-1907	1.6	5
161	GaSb-based VCSELs emitting in the mid-infrared wavelength range (2–3 μm) grown by MBE. *Journal of Crystal Growth*, **2009**, 311, 1912-1916	1.6	22
160	Mid-infrared GaSb-based EP-VCSEL emitting at 2.63 [micro sign]m. *Electronics Letters*, **2009**, 45, 265	1.1	24
159	Room-temperature operation of a 2.25 μm electrically pumped laser fabricated on a silicon substrate. *Applied Physics Letters*, **2009**, 94, 061124	3.4	35
158	Mid-IR lasing from highly tensile-strained, type II, GaInAs/GaSb quantum wells. *Electronics Letters*, **2009**, 45, 1320	1.1	4
157	GaSb-based, 2.2 μm type-I laser fabricated on GaAs substrate operating continuous wave at room temperature. *Applied Physics Letters*, **2009**, 94, 023506	3.4	35
156	Subpicosecond timescale carrier dynamics in GaInAsSb/AlGaAsSb double quantum wells emitting at 2.3 μm. *Applied Physics Letters*, **2008**, 92, 101931	3.4	19
155	S20 photocathodes grown by molecular-beam deposition. *Electronics Letters*, **2008**, 44, 315	1.1	1
154	Type II transition in InSb-based nanostructures for midinfrared applications. *Journal of Applied Physics*, **2008**, 103, 114516	2.5	9
153	Transmission Electron Microscopy Study of Sb-Based Quantum Dots. *Springer Proceedings in Physics* , **2008**, 251-254	0.2	
152	High-density InSb-based quantum dots emitting in the mid-infrared. *Journal of Crystal Growth*, **2007** , 301-302, 713-717	1.6	17
151	Growth and characterization of GaInSb/GaInAsSb hole-well laser diodes emitting near 2.93 μm. *Journal of Crystal Growth*, **2007**, 301-302, 967-970	1.6	3
150	Interface analysis of InAs/GaSb superlattice grown by MBE. *Journal of Crystal Growth*, **2007**, 301-302, 889-892	1.6	42
149	Investigations of InSb-based quantum dots grown by molecular-beam epitaxy. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2007**, 4, 1743-1746		1
148	MBE growth and interface formation of compound semiconductor heterostructures for optoelectronics. *Physica Status Solidi (B): Basic Research*, **2007**, 244, 2683-2696	1.3	9
147	InAs/GaSb short-period superlattice injection lasers operating in 2.5 [micro sign]m–3.5 [micro sign]m mid-infrared wavelength range. *Electronics Letters*, **2007**, 43, 1285	1.1	12

146	Conduction-band crossover induced by misfit strain in InSb□GaSb self-assembled quantum dots. *Physical Review B*, **2007**, 76,	3.3	8
145	Molecular-beam epitaxy of InSb/GaSb quantum dots. *Journal of Applied Physics*, **2007**, 101, 124309	2.5	28
144	Correlation between quantum well morphology, carrier localization and the optoelectronic properties of GaInNAs/GaAs light emitting diodes. *Semiconductor Science and Technology*, **2006**, 21, 1047-1052	1.8	4
143	High-density, uniform InSb□GaSb quantum dots emitting in the midinfrared region. *Applied Physics Letters*, **2006**, 89, 263118	3.4	23
142	Structural and optical properties of InSb quantum dots for mid-IR applications. *Physica Status Solidi (B): Basic Research*, **2006**, 243, 3959-3962	1.3	8
141	LO multi-phonons cooperative phenomenon in ZnSe□BeSemixed crystals. *Journal of Physics and Chemistry of Solids*, **2005**, 66, 2099-2103	3.9	4
140	Percolation picture for long wavelength phonons in zinc blende alloys: application to GaInAs. *Journal of Physics and Chemistry of Solids*, **2005**, 66, 2094-2098	3.9	
139	Decomposition in as-grown (Ga,In)(N,As) quantum wells. *Applied Physics Letters*, **2005**, 87, 171901	3.4	37
138	Correlation between interface structure and light emission at 1.3□1.55 □m of (Ga,In)(N,As) diluted nitride heterostructures on GaAs substrates. *Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena*, **2004**, 22, 2195		33
137	Long-wave phonons in ZnSe□BeSe mixed crystals: Raman scattering and percolation model. *Physical Review B*, **2004**, 70,	3.3	27
136	Be□Se double-phonon behavior in Zn1□□MgyBexSe alloy. *Journal of Applied Physics*, **2004**, 95, 7690-7693	2.5	4
135	Carrier recombination processes in GaAsN: from the dilute limit to alloying. *IEE Proceedings: Optoelectronics*, **2004**, 151, 365-368		4
134	Percolation-based multimode GaN behaviour in the Raman spectra of GaInAsN. *IEE Proceedings: Optoelectronics*, **2004**, 151, 338-341		
133	Giant LO oscillation in the Zn1□Bex(Se,Te) multi-phonons percolative alloys. *Thin Solid Films*, **2004**, 450, 195-198	2.2	5
132	Does In-bonding delay GaN-segregation in GaInAsN? A Raman study. *Applied Physics Letters*, **2004**, 85, 5872-5874	3.4	10
131	Nanoscale analysis of the In and N spatial redistributions upon annealing of GaInNAs quantum wells. *Applied Physics Letters*, **2004**, 84, 2503-2505	3.4	54
130	From GaAs:N to oversaturated GaAsN: Analysis of the band-gap reduction. *Physical Review B*, **2004**, 69,	3.3	32
129	Dominant carrier recombination mechanisms in GaInNAs□GaAs quantum well light-emitting diodes. *Applied Physics Letters*, **2004**, 85, 40-42	3.4	7

128	Bi-modal Raman response of BeSe vibration in Zn1−yMgyBexSe alloys. *Journal of Alloys and Compounds*, **2004**, 382, 271-274	5.7	7
127	Effect of nitrogen on the band structure and material gain of In/sub y/Ga/sub 1-y/As/sub 1-x/Nx-GaAs quantum wells. *IEEE Journal of Selected Topics in Quantum Electronics*, **2003**, 9, 716-722	3.8	15
126	Correlations between structural and optical properties of GaInNAs quantum wells grown by MBE. *Journal of Crystal Growth*, **2003**, 251, 383-387	1.6	31
125	Percolation context in mixed crystals with mechanical contrast. *Journal of Physics and Chemistry of Solids*, **2003**, 64, 1585-1590	3.9	2
124	LO phonon–plasmon coupling and mechanical disorder-induced effect in the Raman spectra of GaAsN alloys. *Solid-State Electronics*, **2003**, 47, 455-460	1.7	4
123	Photoluminescence spectroscopy of Ga(In)NAs quantum wells for emission at 1.5 μm. *Solid-State Electronics*, **2003**, 47, 477-482	1.7	11
122	Coexistence in photoluminescence of free exciton and bound exciton in low nitrogen content GaInNAs layers. *Physica Status Solidi C: Current Topics in Solid State Physics*, **2003**, 2631-2634		
121	Nanoindentation of Si, GaP, GaAs and ZnSe single crystals. *Journal Physics D: Applied Physics*, **2003**, 36, L5-L9	3	59
120	Annealing effects on the crystal structure of GaInNAs quantum wells with large In and N content grown by molecular beam epitaxy. *Journal of Applied Physics*, **2003**, 94, 2319-2324	2.5	56
119	GaInNAs/GaAs quantum wells grown by molecular-beam epitaxy emitting above 1.5 μm. *Applied Physics Letters*, **2003**, 82, 1845-1847	3.4	37
118	Percolation-based vibrational picture to estimate nonrandom N substitution in GaAsN alloys. *Applied Physics Letters*, **2003**, 82, 2808-2810	3.4	17
117	Isoelectronic traps in heavily doped GaAs:(In,N). *Physical Review B*, **2003**, 68,	3.3	14
116	Interplay between the growth temperature, microstructure, and optical properties of GaInNAs quantum wells. *Applied Physics Letters*, **2003**, 82, 3451-3453	3.4	32
115	Raman study of Zn1−xBexSe/GaAs systems with low Be-content (x≤0.31). *Thin Solid Films*, **2002**, 403-404, 530-534	2.2	1
114	LO phonon-plasmon coupling in N-doped Zn1−xBex Se/GaAs (x≤0.15). *Thin Solid Films*, **2002**, 403-404, 535-538	2.2	
113	Vibrational Evidence for Percolative Behavior in ZnBeSe. *Physica Status Solidi (B): Basic Research*, **2002**, 229, 25-29	1.3	6
112	Self-Compensation of the Phosphorus Acceptor in ZnSe. *Physica Status Solidi (B): Basic Research*, **2002**, 229, 251-255	1.3	3
111	Displaced Substitutional Phosphorus Acceptors in Zinc Selenide. *Physica Status Solidi (B): Basic Research*, **2002**, 229, 257-260	1.3	4

110	Light-Hole and Heavy-Hole Excitons: the Right Probe for the Physics of Low N Content GaAsN. *Physica Status Solidi (B): Basic Research*, **2002**, 234, 778-781	1.3	1
109	Electronic structure and radiative lifetimes of ideal Zn1−xBexSe alloys. *Solid State Communications*, **2002**, 123, 209-212	1.6	11
108	Mechanisms affecting the photoluminescence spectra of GaInNAs after post-growth annealing. *Applied Physics Letters*, **2002**, 80, 4148-4150	3.4	79
107	Nanoindentation study of Zn1−xBexSe heteroepitaxial layers. *Journal Physics D: Applied Physics*, **2002**, 35, 3015-3020	3	24
106	Raman study of Zn1−xBexSe/GaAs systems with low Be content (x?0.20). *Journal of Applied Physics*, **2002**, 91, 9187-9197	2.5	14
105	Raman study of ZnxBe1−xSe solid solutions. *Optical Materials*, **2001**, 17, 323-326	3.3	5
104	Wide-band-gap ZnMgBeSe alloys grown onto GaAs by molecular beam epitaxy. *Journal of Crystal Growth*, **2001**, 223, 461-465	1.6	8
103	Direct evidence for the trigonal symmetry of shallow phosphorus acceptors in ZnSe. *Physical Review B*, **2001**, 64,	3.3	8
102	On the origin of carrier localization in Ga1−xInxNyAs1−y/GaAs quantum wells. *Applied Physics Letters*, **2001**, 78, 1562-1564	3.4	121
101	Visible-blind ultraviolet photodetectors based on ZnMgBeSe Schottky barrier diodes. *Applied Physics Letters*, **2001**, 78, 4190-4192	3.4	24
100	Vibrational evidence for a percolative behavior in Zn1−xBexSe. *Physical Review B*, **2001**, 65,	3.3	33
99	Influence of alloy stability on the photoluminescence properties of GaAsN/GaAs quantum wells grown by molecular beam epitaxy. *Applied Physics Letters*, **2001**, 79, 3404-3406	3.4	38
98	Evaluation of the potential of ZnSe and Zn(Mg)BeSe compounds for ultraviolet photodetection. *IEEE Journal of Quantum Electronics*, **2001**, 37, 1146-1152	2	30
97	ZnSe- and ZnMgBeSe-Based Schottky Barrier Photodetectors for the Blue and Ultraviolet Spectral Range. *Physica Status Solidi A*, **2000**, 180, 301-305		3
96	Molecular beam epitaxial growth and characterization of Be(Zn)Se on Si(0 0 1) and GaAs(0 0 1). *Journal of Crystal Growth*, **2000**, 214-215, 95-99	1.6	10
95	Hydrogen/deuterium: a probe to investigate carrier-compensation in ZnSe : N. *Journal of Crystal Growth*, **2000**, 214-215, 507-510	1.6	3
94	Molecular beam epitaxy of ZnxBe1−xSe: Influence of the substrate nature and epilayer properties. *Journal of Electronic Materials*, **2000**, 29, 883-886	1.9	5
93	ZnSe-based Schottky barrier photodetectors. *Electronics Letters*, **2000**, 36, 352	1.1	18

92	Transmission electron microscopy study of crystal defects in ZnSe/GaAs(001) epilayers. *Journal of Physics Condensed Matter*, **2000**, 12, 10287-10293	1.8	5
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